

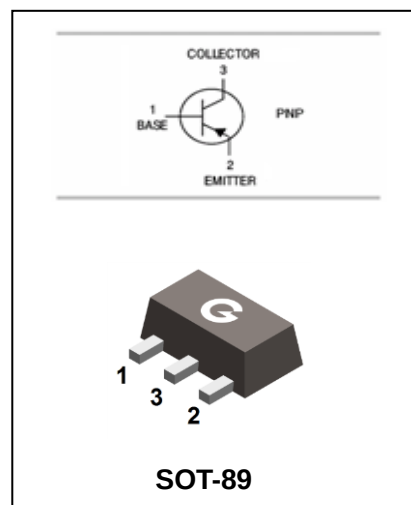
Power Transistor(-80V,-1A)

T2SB1260

FEATURES

- High breakdown voltage and high current
 $BV_{CEO}=-80V, I_C=-1A$
- Good h_{FE} Linearity
- Low $V_{CE(sat)}$
- Complements the T2SD1898
- Halogen free
- RoHS compliant with Halogen-free
- Qualified to AEC-Q101 Standards

HF



APPLICATIONS

- Epitaxial planar type PNP silicon transistor

ORDERING INFORMATION

Type No.	Marking	Package Code
T2SB1260-Q	ZL	SOT-89
T2SB1260-R	ZL	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –DC –Pulse	-1 -2	A
P_c	Collector power Dissipation	0.5	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to +150	°C

*1: When mounted on a 40*40*0.7mm ceramic board.

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A$ $I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA$ $I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A$ $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V$ $I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V$, $I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -3V$ $I_C = -0.1A$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA$ $I_B = -50mA$			-0.4	V
Output Capacitance	C_{obo}	$V_{CB} = -10V$ $f = 1.0MHz$ $I_E = 0$	-	20		pF

CLASSIFICATION H_{FE}

Rank	Q	R
Range	120-270	180-390

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TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

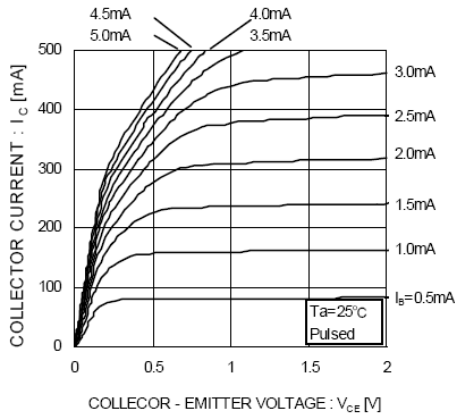


Fig.1 Ground Emitter Output Characteristics

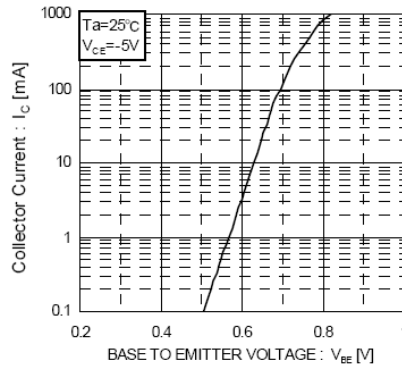


Fig.2 Grounded Emitter Propagation Characteristics

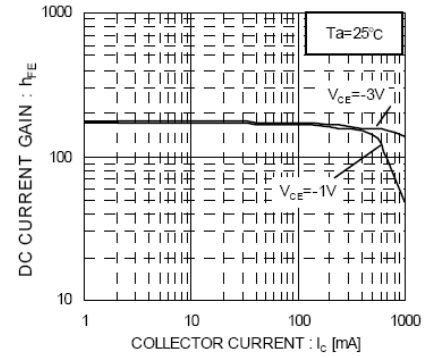


Fig.3 DC Current Gain vs Collector Current

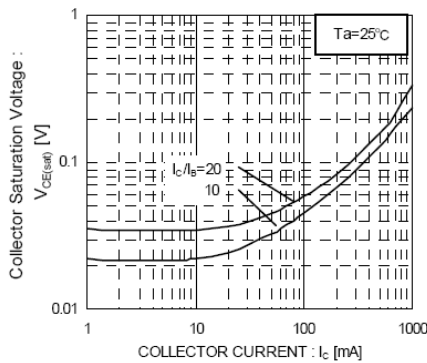


Fig.4 Collector-Emitter Saturation Voltage vs Collector Current

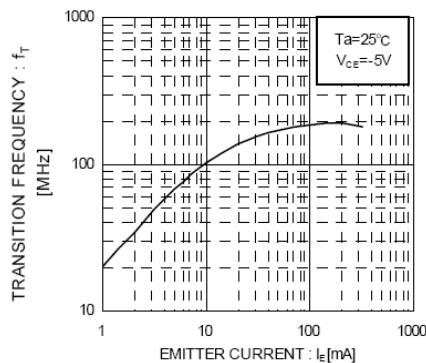


Fig.5 Transition Frequency vs Emitter Current

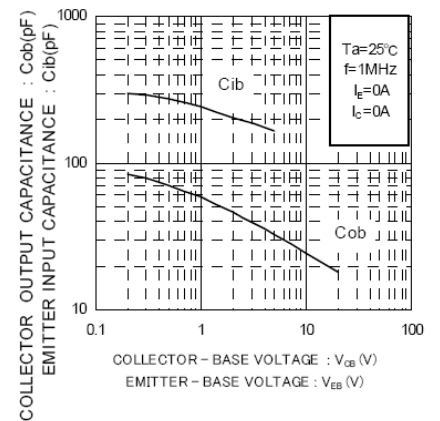


Fig.6 Emitter Input Capacitance vs. Emitter-Base Voltage
Collector Output Capacitance vs. Collector-Base

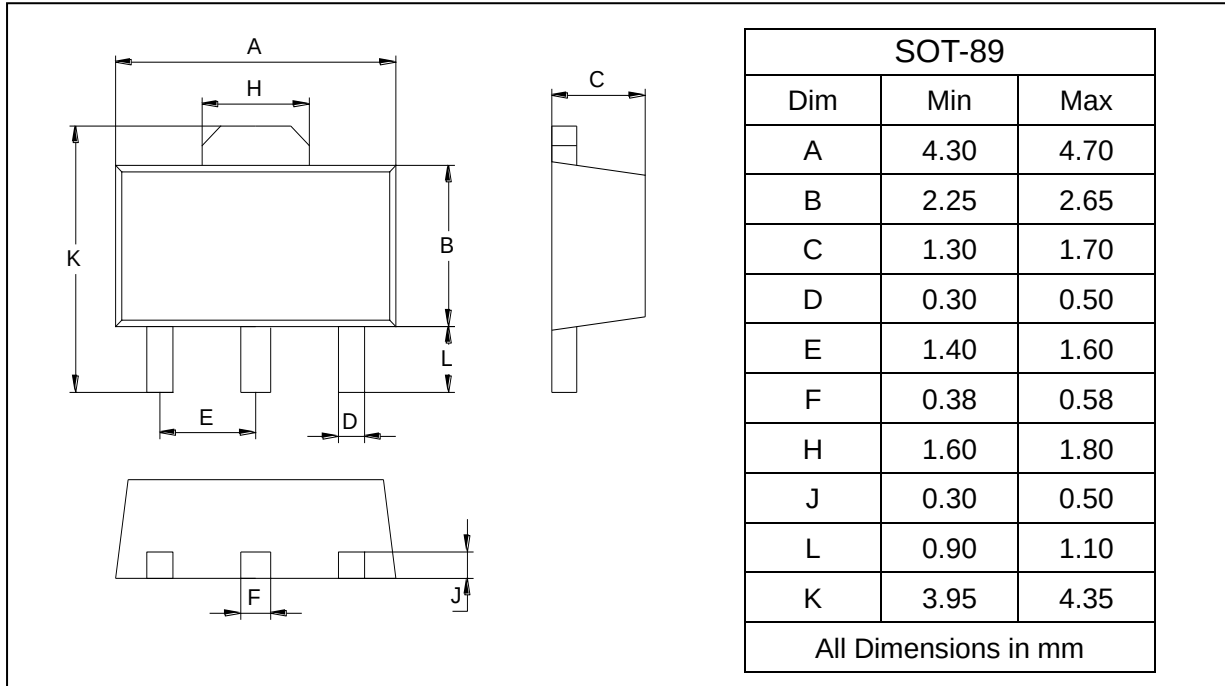
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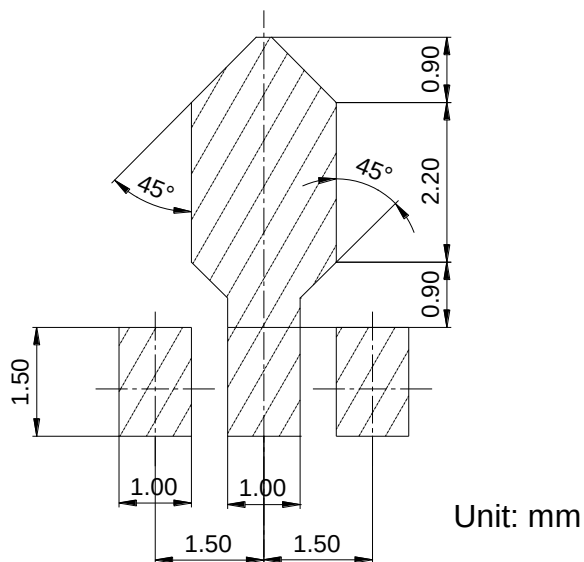
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
T2SB1260	SOT-89	1000 pcs / Tape & Reel